

MS 23N18

N-Channel 30-V (D-S) MOSFET

Description

These miniature surface mount MOSFETs utilize High Cell Density process. Low rDS(on) assures minimal power loss and conserves energy, making this device ideal for use in power management circuitry. Typical applications are lower voltage application, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

Features

- Low rDS(on) trench technology
- Low thermal impedance
- Fast switching speed
- RoHS compliant package

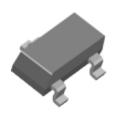
Typical Applications:

- White LED boost converters
- Automotive Systems
- Industrial DC/DC Conversion Circuits

Package type: SOT-23

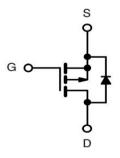
Packing & Order Information

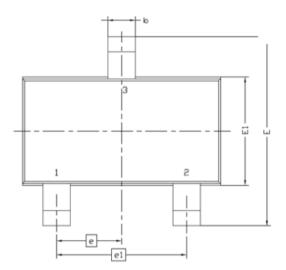
3,000/Reel

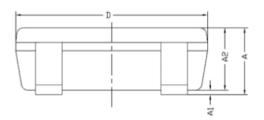


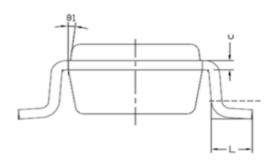
RoHS

Graphic symbol









Symbol	MILLIMETERS			
Symbol	MIN	MAX		
Α	8.0	1.2		
A1	0	0.1		
A2	0.7	1.1		
b	0.3	0.5		
С	0.1	0.2		
D	2.7	3.1		
E	2.6	3		
E1	1.4	1.8		
е	0.95 BSC			
e1	1.9 BSC			
L	0.3	0.6		
θ1	7° NOM			



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MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

Absolute N	Absolute Maximum Ratings (Tc=25°C unless otherwise specified)					
Symbol	Parameter	Value	Unit			
V_{DS}	Drain-Source Voltage	30	V			
V_{GS}	Gate-Source Voltage	±20	V			
I.	Continuous Drain Current ^a (T _A =25°C)	2.4	A			
\mathbf{I}_{D}	Continuous Drain Current ^a (T _A =70°C)	1.9	A			
I_{DM}	Pulsed Drain Current ^b	10	A			
Is	Continuous Source Current (Diode Conduction) ^a	1.9	A			
D	Power Dissipation ^a (T _A =25°C)	1.3	W			
P_D	Power Dissipation ^a (T _A =70°C)	0.8	W			
$T_{\rm J}/T_{\rm STG}$	Operating Junction and Storage Temperature	-55 to +150	°C			

Thermal Resistance Ratings					
Symbol	Parameter Maximum Unit				
R _{θJ A}	Maximum Junction-to-Ambient C/W ^a (t <= 10 sec)	100	°C/W		
	Maximum Junction-to-Ambient C/W ^a (Steady-State)	166	C/ W		

Notes

- a. Surface Mounted on 1" x 1" FR4 Board.
- b. Pulse width limited by maximum junction temperature

Electrical Characteristics						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS},I_{D}\!=$ -250 μA	1			V
I_{GSS}	Gate-Body Leakage	$V_{DS} = 0 V$, $V_{GS} = \pm 20 V$			±100	nA
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS} = 24 \ V$, $V_{GS} = 0 \ V$ $V_{DS} = 24 \ V$, $V_{GS} = 0 \ V$, $T_{J} = 55 \ ^{\circ}C$			1 25	uA
I _{D(on)}	On-State Drain Current ^A	$V_{DS}=5\ V\ ,\ V_{GS}=10\ V$	5			A
rDS (on)	Drain-Source On-Resistance ^A	$V_{DS} = 10 \text{ V}, I_{D} = 1.9 \text{ A}$ $V_{DS} = 4.5 \text{ V}, I_{D} = 1.6 \text{ A}$			160 250	mΩ
gfs	Forward Tranconductance ^A	$V_{GS} = 15 \text{ V}, I_{D} = 1.9 \text{ A}$		6		S
V _{SD}	Diode Forward Voltage	$I_S = 0.95 \text{ A}$, $V_{GS} = 0 \text{ V}$		0.84		V



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Dyna mic ^b						
Symbol	Parameter	Test Conditions	Min	Тур.	Max.	Units
Q_g	Total Gate Charge	$V_{DS} = 15 \text{ V}, I_{D} = 1.9 \text{ A},$ $V_{GS} = 4.5 \text{ V}$		1.4		nC
$Q_{\rm gs}$	Gate-Source Charge			0.4		nC
Q_{gd}	Gate-Drain Charge			0.7		nC
$t_{d(on)}$	Turn-On Delay Time	$V_{DS} = 15 \ V \ , \ I_D = 1.9 \ A \ , \\ V_{GEN} = 10 \ V \ , \ R_L = 7.9 \ \Omega \ , \\ R_{GEN} = 6 \ \Omega$		2		ns
$t_{\rm r}$	Rise Time			5		ns
$t_{\rm d(off)}$	Turn-Off Delay Time			12		ns
tf	Fall Time			4		ns
C _{ISS}	Input Capacitance	$V_{DS} = 15 \ V \ , \ V_{GS} = 0 \ V \ , \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \$		103		pF
Coss	Output Capacitance			21		pF
C _{RSS}	Reverse Transfer Capacitance			16		pF

Notes

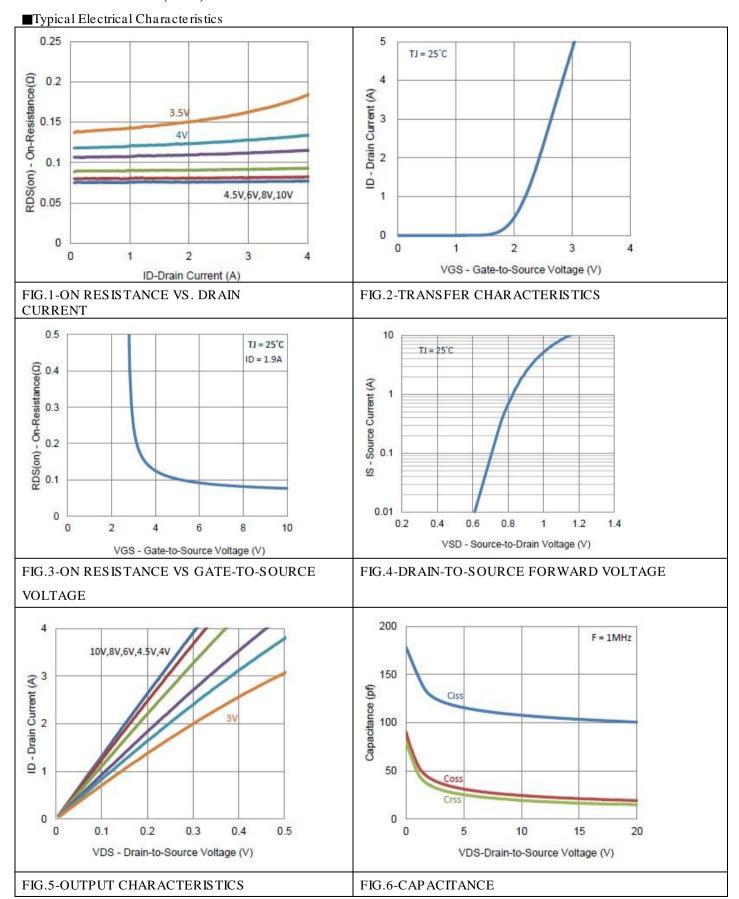
a. Pulse test: PW <= 300us duty cycle <= 2%.

b. Guaranteed by design, not subject to production testing.



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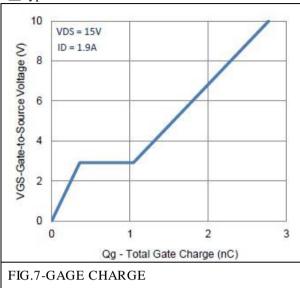


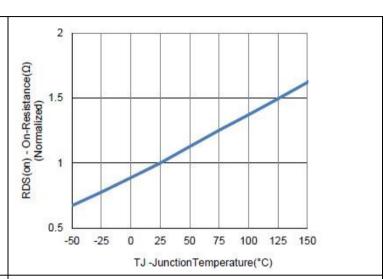


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■Typical Electrical Characteristics





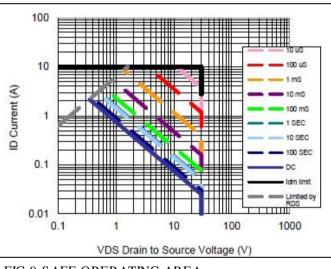


FIG.8-NORMALIZED ON-RESISTANCE VS JUNCTION TMPERATURE

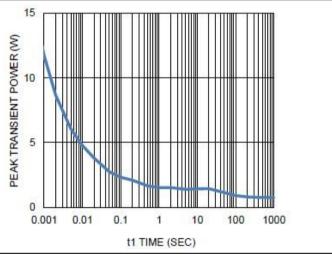


FIG.9-SAFE OPERATING AREA



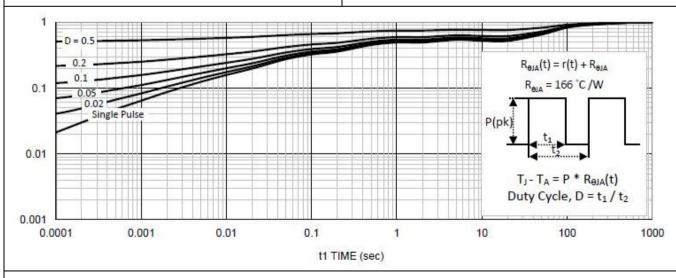


FIG.11-NORMALIZED THERMAL TRANSIENT JUNCTION TO AMBIENT



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